

Moiré-Modulated Conductance of Hexagonal Boron N

Nano Letters

18, 4241-4246

DOI: 10.1021/acs.nanolett.8b01223

Citation Report

#	ARTICLE	IF	CITATIONS
1	Transfer-Free Synthesis of Lateral Graphene-Hexagonal Boron Nitride Heterostructures from Chemically Converted Epitaxial Graphene. <i>Advanced Materials Interfaces</i> , 2019, 6, 1900419.	1.9	10
2	Large-area adlayer-free single-layer h-BN film achieved by controlling intercalation growth. <i>Applied Surface Science</i> , 2019, 498, 143851.	3.1	9
3	Nucleation and growth of atomically thin hexagonal boron nitride on Ni/MgO(111) by molecular beam epitaxy. <i>Journal of Applied Physics</i> , 2019, 125, .	1.1	13
4	GaN-Based Nanorods/Graphene Heterostructures for Optoelectronic Applications. <i>Physica Status Solidi (B): Basic Research</i> , 2019, 256, 1800454.	0.7	5
5	Valley-polarized tunneling currents in bilayer graphene tunneling transistors. <i>Physical Review B</i> , 2019, 99, .	1.1	8
6	Strain Engineering of 2D Materials: Issues and Opportunities at the Interface. <i>Advanced Materials</i> , 2019, 31, e1805417.	11.1	415
7	Hexagonal boron nitride monolayers on metal supports: Versatile templates for atoms, molecules and nanostructures. <i>Surface Science Reports</i> , 2019, 74, 1-95.	3.8	184
8	Understanding Interlayer Contact Conductance in Twisted Bilayer Graphene. <i>Small</i> , 2020, 16, e1902844.	5.2	27
9	Influence of Proximity to Supporting Substrate on van der Waals Epitaxy of Atomically Thin Graphene/Hexagonal Boron Nitride Heterostructures. <i>ACS Applied Materials & Interfaces</i> , 2020, 12, 8897-8907.	4.0	11
10	Step-flow growth of graphene-boron nitride lateral heterostructures by molecular beam epitaxy. <i>2D Materials</i> , 2020, 7, 035014.	2.0	14
11	Building Functional Memories and Logic Circuits with 2D Boron Nitride. <i>Advanced Functional Materials</i> , 2021, 31, 2004733.	7.8	22
12	Coherent Electronic Band Structure of $\text{TiTe}_2/\text{TiSe}_2$ Moiré Bilayer. <i>ACS Nano</i> , 2021, 15, 3359-3364.	7.3	7
13	Mechanically sensing and tailoring electronic properties in two-dimensional atomic membranes. <i>Current Opinion in Solid State and Materials Science</i> , 2021, 25, 100900.	5.6	7
14	Band gap measurements of monolayer h-BN and insights into carbon-related point defects. <i>2D Materials</i> , 2021, 8, 044001.	2.0	34
15	Exciton and Phonon Radiative Linewidths in Monolayer Boron Nitride. <i>Physical Review X</i> , 2022, 12, .	2.8	5
16	2+ <i>i>Î</i>â€Dimensional Materials via Atomistic Zâ€Welding. <i>Advanced Science</i>, 2022, 9, .</i>	5.6	8